DF252

FAST RECOVERY DIODE

APPLICATIONS

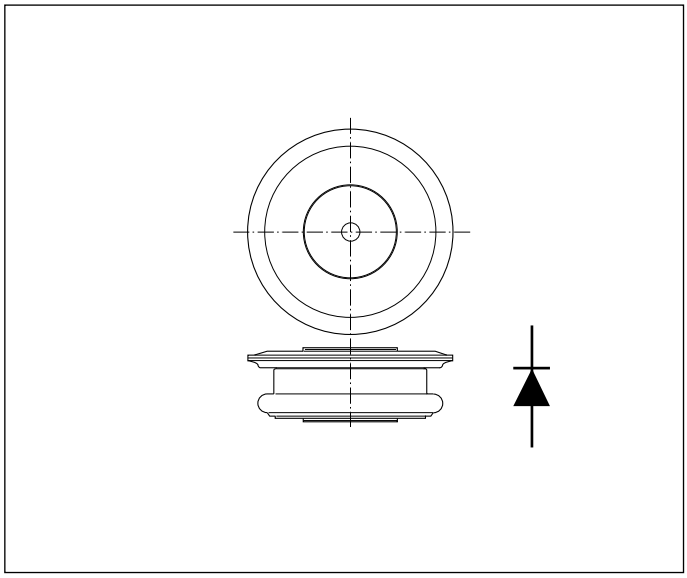
- Induction Heating.
- A.C. Motor Drives.
- Inverters And Choppers.
- Welding.
- High Frequency Rectification.
- UPS.

KEY PARAMETERS

V_{RRM}	1600V
$I_{F(AV)}$	360A
I_{FSM}	3000A
Q_r	35μC
t_{rr}	3.2μs

FEATURES

- Double Side Cooling.
- High Surge Capability.
- Low Recovery Charge.



Outline type code: M771. Turn to page 8 for further information.

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V_{RRM} V	Conditions
DF252 16	1600	$V_{RSM} = V_{RRM} + 100V$
DF252 14	1400	
DF252 12	1200	
DF252 10	1000	
DF252 08	800	
DF252 06	600	

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, T_{case} = 65°C	360	A
$I_{F(RMS)}$	RMS value	T_{case} = 65°C	560	A
I_F	Continuous (direct) forward current	T_{case} = 65°C	500	A
Single Side Cooled (Anode side)				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, T_{case} = 65°C	276	A
$I_{F(RMS)}$	RMS value	T_{case} = 65°C	435	A
I_F	Continuous (direct) forward current	T_{case} = 65°C	375	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 0% $V_{RRM,}$ T_j = 150ºC	3.0	kA
I^2t	I^2t for fusing		45×10^3	A^2s
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 50% $V_{RRM,}$ T_j = 150ºC	2.4	kA
I^2t	I^2t for fusing		28.8×10^3	A^2s

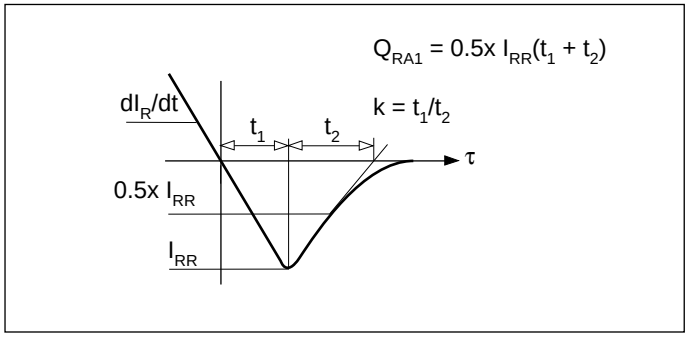
THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.07	ºC/W
		Single side cooled	Anode dc	-	0.133	ºC/W
			Cathode dc	-	0.147	ºC/W
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 3.5kN with mounting compound	Double side	-	0.02	ºC/W
			Single side	-	0.04	ºC/W
T_{vj}	Virtual junction temperature	On-state (conducting)		-	150	ºC
T_{stg}	Storage temperature range			-55	150	ºC
-	Clamping force			3.0	4.0	kN

CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units
V_{FM}	Forward voltage	At 450A peak, T_{case} = 25°C	-	1.6	V
I_{RRM}	Peak reverse current	At V_{RRM}, T_{case} = 125°C	-	20	mA
t_{rr}	Reverse recovery time	I_F = 750A, di_{RR}/dt = 100A/µs T_{case} = 125°C, V_R = 100V	3.2	-	µs
Q_{RA1}	Recovered charge (50% chord)		-	35	µC
I_{RM}	Reverse recovery current		-	21	A
K	Soft factor		1.5	-	-
V_{TO}	Threshold voltage	At T_{vj} = 150°C	-	1.0	V
r_T	Slope resistance	At T_{vj} = 150°C	-	1.33	mΩ
V_{FRM}	Forward recovery voltage	di/dt = 1000A/µs, T_j = 125°C	-	50	V

DEFINITION OF K FACTOR AND Q_{RA1}



CURVES

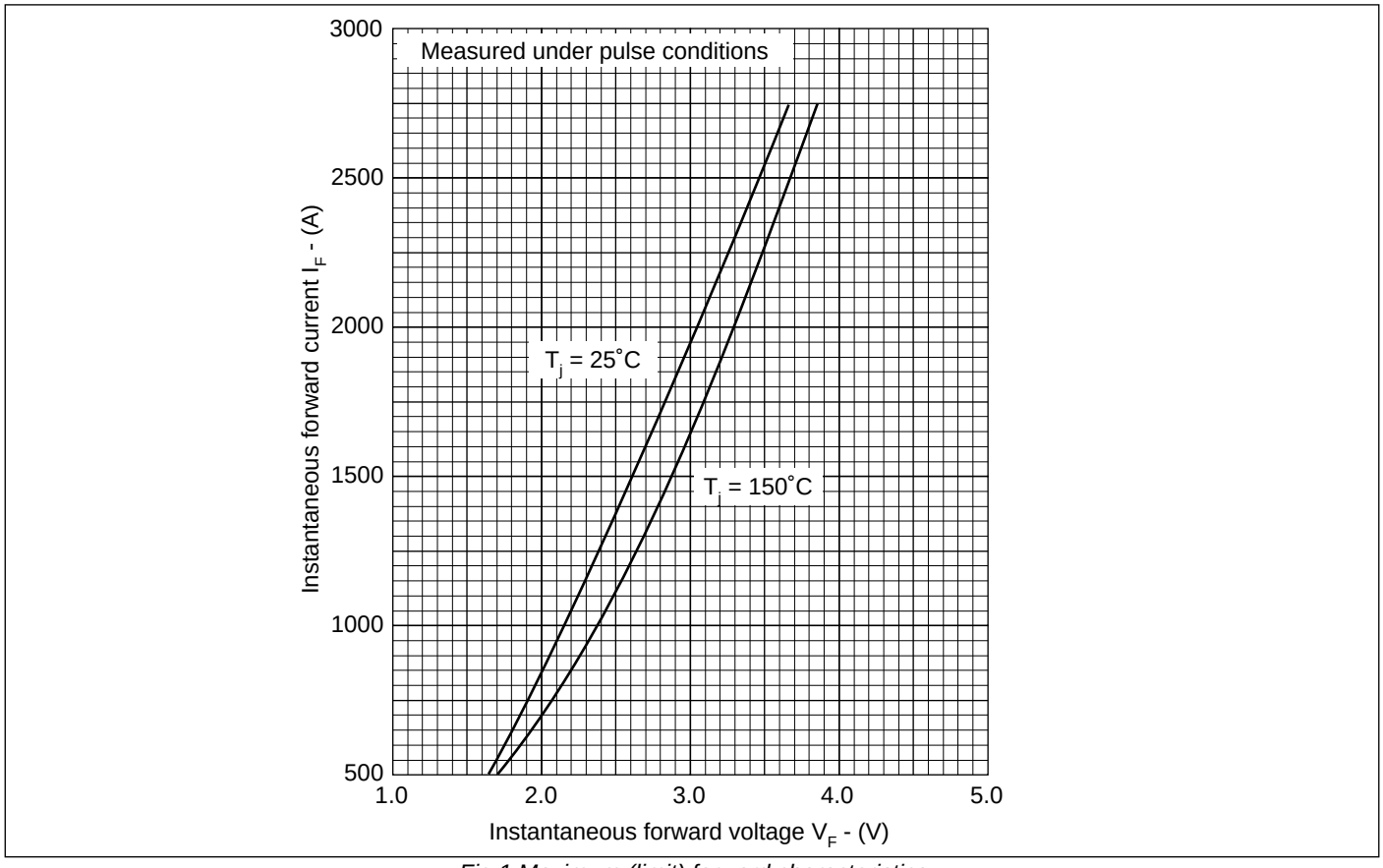


Fig.1 Maximum (limit) forward characteristics

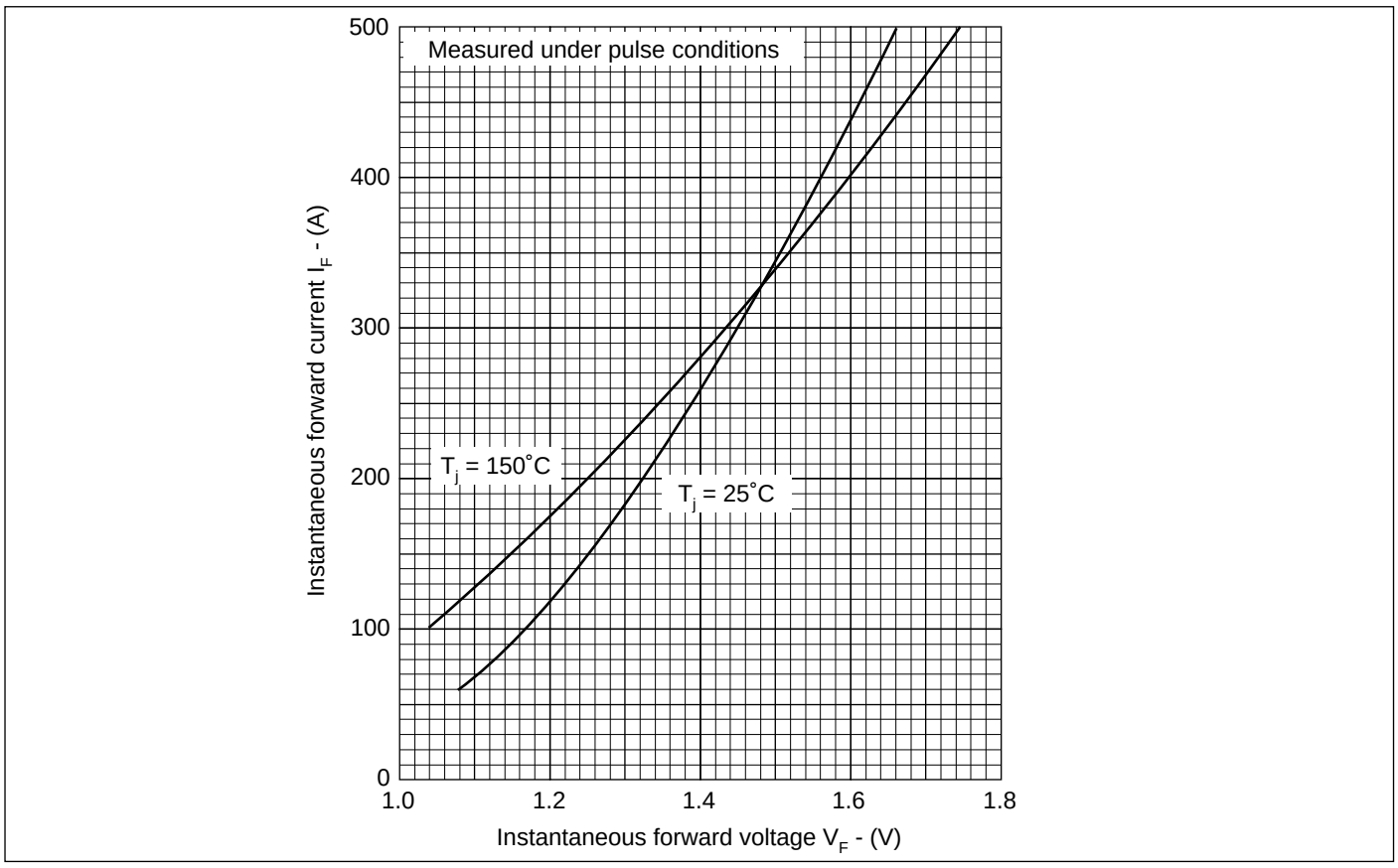


Fig.2 Maximum (limit) forward characteristics

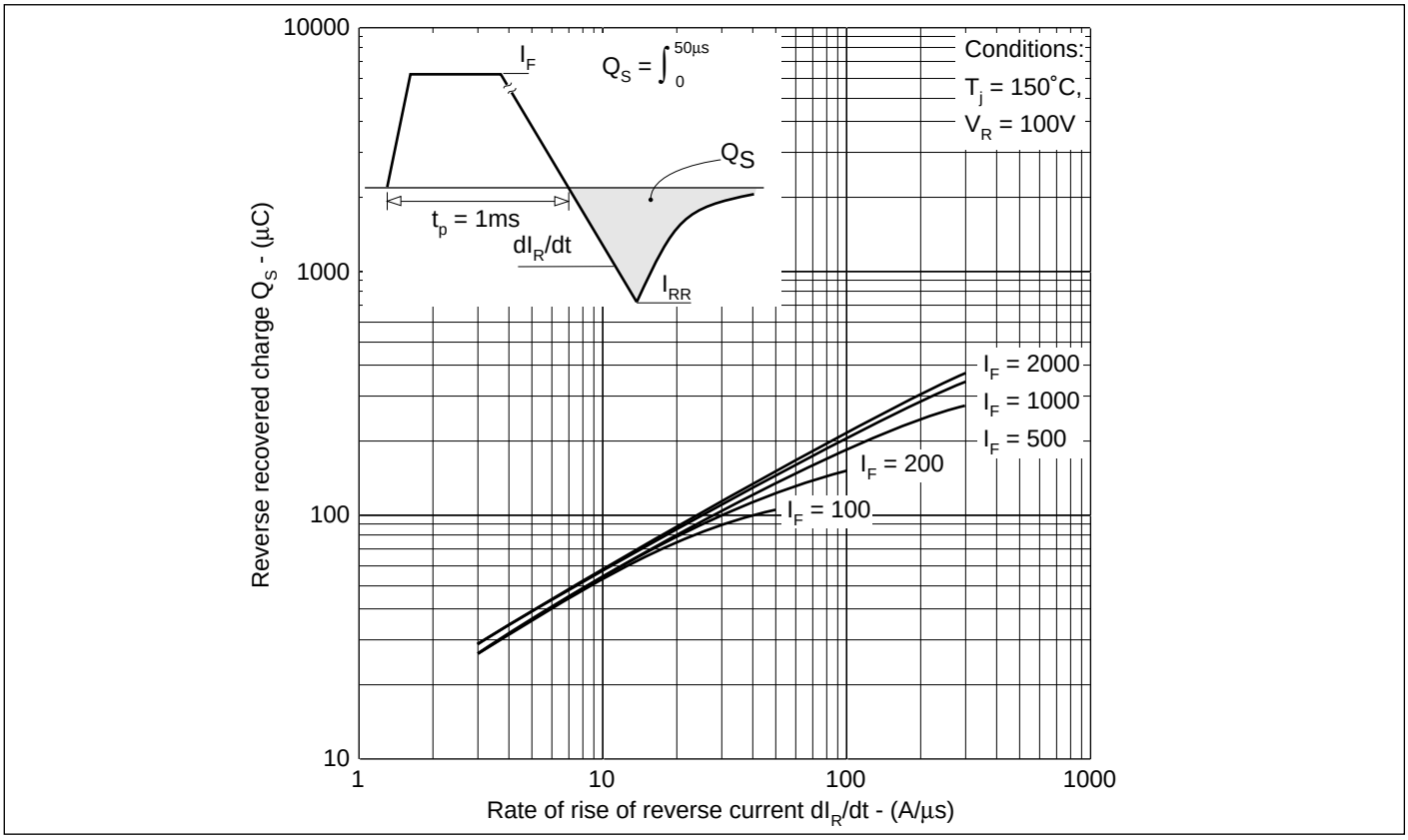


Fig.3 Recovered charge

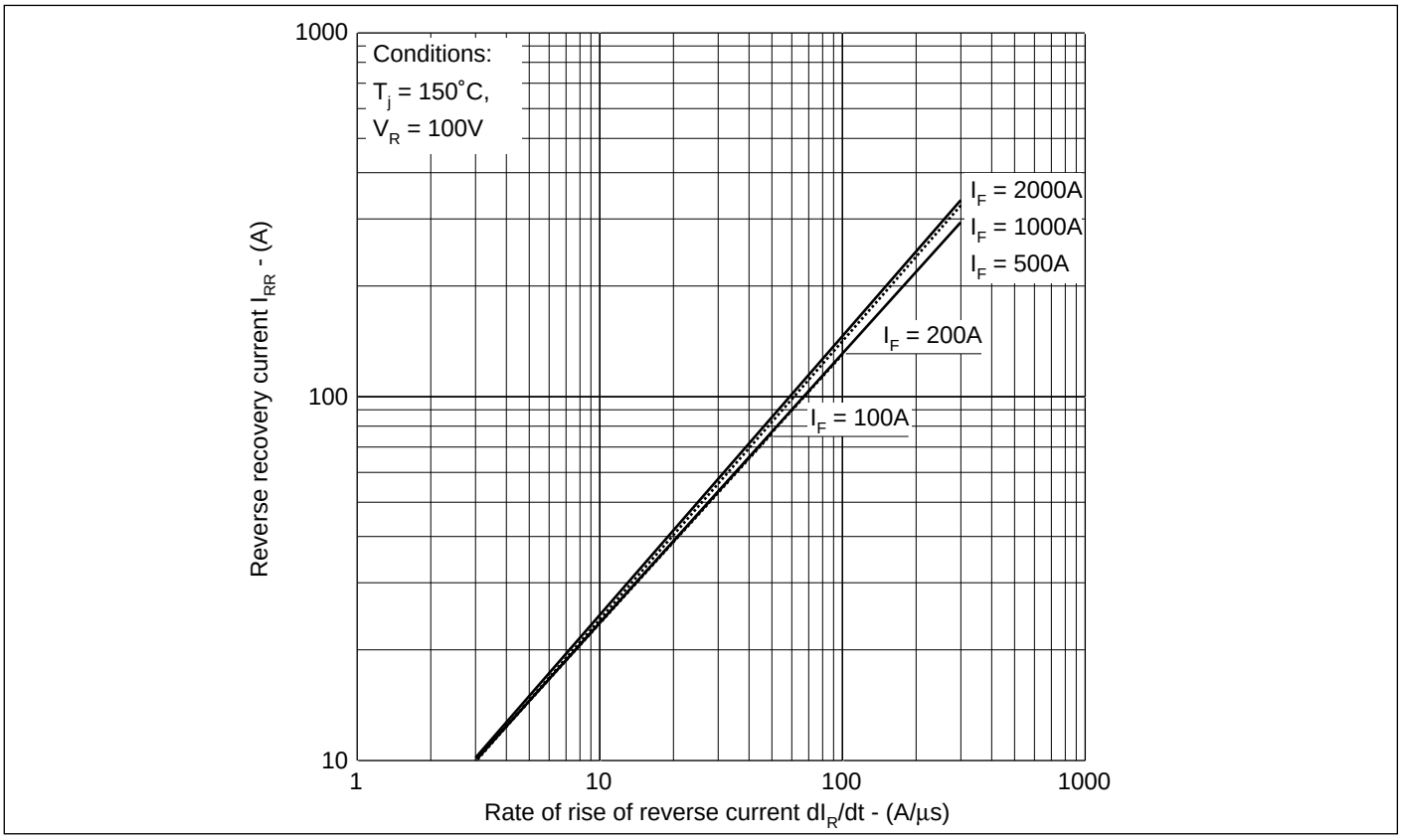


Fig.4 Typical reverse recovery current vs rate of fall of forward current

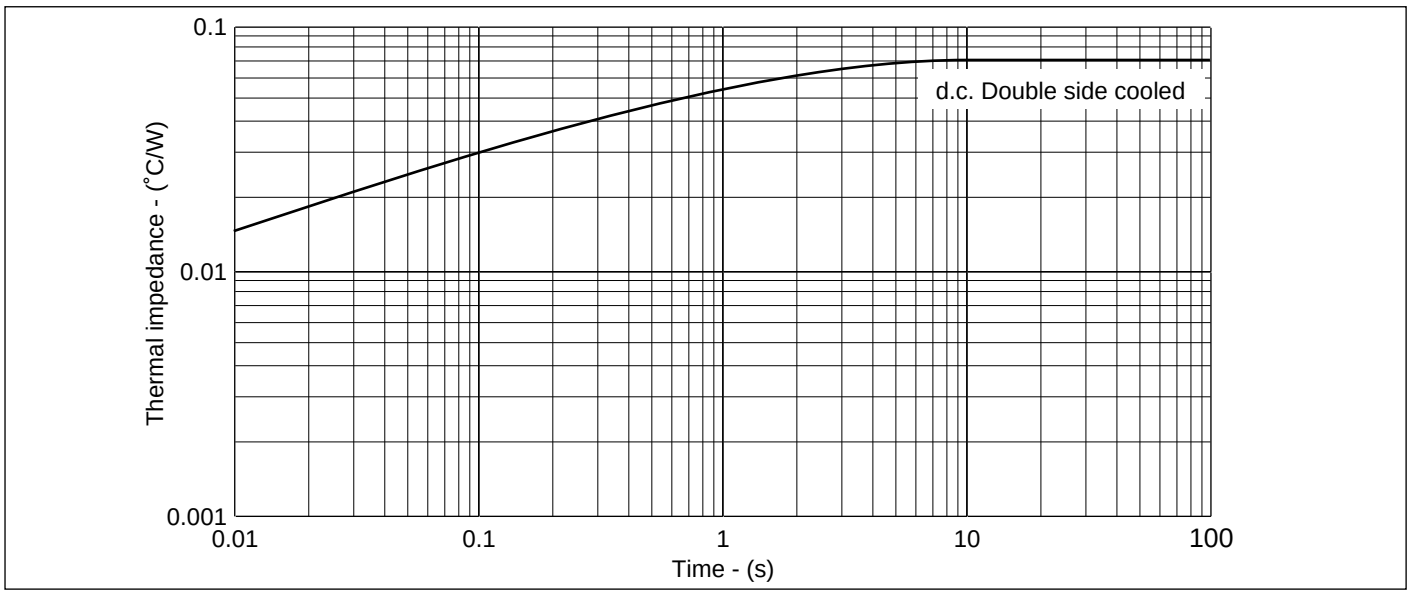
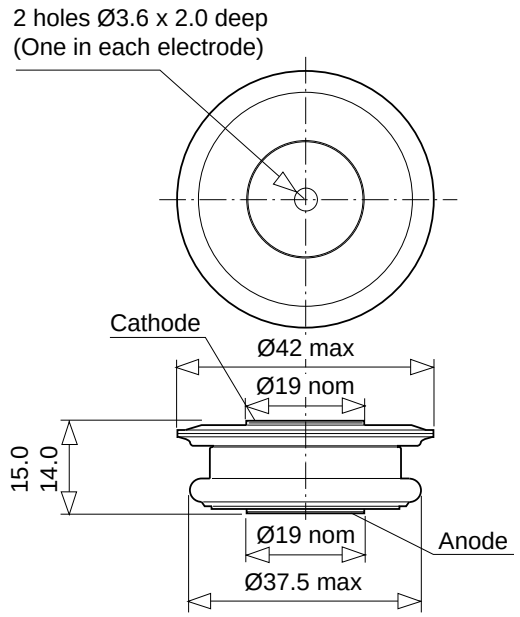


Fig.5 Maximum (limit) transient thermal impedance - junction to case - (˚C/W)

PACKAGE DETAILS - M771

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



Weight: 50g

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